1N831

SILICON MIXER DIODE

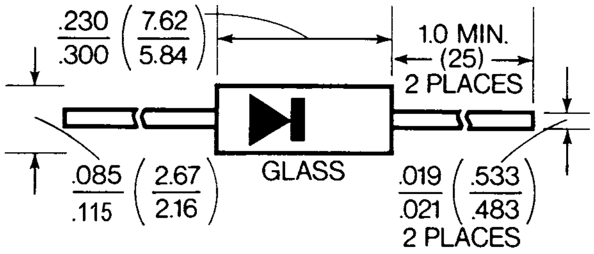
DESCRIPTION:

The **ASI 1N831** is a Silicon Mixer Diode Designed for Applications Operating From 2.0 to 4.0 GHz.

FEATURES:

- High burnout resistance
- Low noise figure
- Hermetically sealed package

PACKAGE STYLE DO- 7



MAXIMUM RATINGS

I_F	20 mA
V_R	1.0 V
P_{DISS}	2.0 (ERGS) @ T_C = 25 °C
T_J	-55 °C to +150 °C
T_{STG}	-55 °C to +150 °C

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIM	UNITS
N_F	f = 3060 MHz P_{LO} = 1.0 mW N_{Fif} = 1.5 dB R_L = 100 Ω I_F = 30 MHz			8.3	**dB**
N_R	f = 3060 MHz P_{LO} = 1.0 mW N_{Fif} = 1.5 dB R_L = 100 Ω I_F = 30 MHz			1.5	**---**
L_C	f = 3060 MHz P_{LO} = 0.5 mW			5.5	**dB**
Z_{IF}	R_L = 22 Ω f = 1000 Hz	300		500	Ω
frange		2.0		4.0	**GHz**